
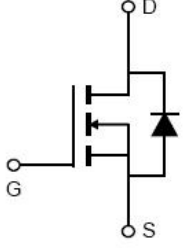


**QIAOXIN N-Channel Super Trench II Power MOSFET**

<p><b>Description</b></p> <p>The series of devices uses <b>Super Trench II</b> technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of <math>R_{DS(ON)}</math> and <math>Q_g</math>. This device is ideal for high-frequency switching and synchronous rectification.</p> <p><b>Application</b></p> <ul style="list-style-type: none"> <li>● DC/DC Converter</li> <li>● Ideal for high-frequency switching and synchronous rectification</li> </ul>	<p><b>General Features</b></p> <ul style="list-style-type: none"> <li>● <math>V_{DS} = 100V, I_D = 65A</math>  <math>R_{DS(ON)} = 9m\Omega</math>, typical@ <math>V_{GS} = 10V</math>  <math>R_{DS(ON)} = 11m\Omega</math>, typical@ <math>V_{GS} = 4.5V</math></li> <li>● Excellent gate charge x <math>R_{DS(on)}</math> product(FOM)</li> <li>● Very low on-resistance <math>R_{DS(on)}</math></li> <li>● 175 °C operating temperature</li> <li>● Pb-free lead plating</li> </ul>
<p><b>TO-220</b></p>  <p><b>Top View</b></p>	 <p><b>Schematic Diagram</b></p>

**Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VCRR095N10A	VCRR095N10A	TO-220	-	-	-

**Absolute Maximum Ratings ( $T_C = 25^\circ C$  unless otherwise noted)**

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	65	A
Drain Current-Continuous( $T_C = 100^\circ C$ )	$I_D(100^\circ C)$	45.5	A
Pulsed Drain Current	$I_{DM}$	260	A
Maximum Power Dissipation	$P_D$	100	W
Derating factor		0.6	W/°C
Single pulse avalanche energy (Note 4)	$E_{AS}$	288	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175	°C

**Thermal Characteristic**

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.67	°C/W
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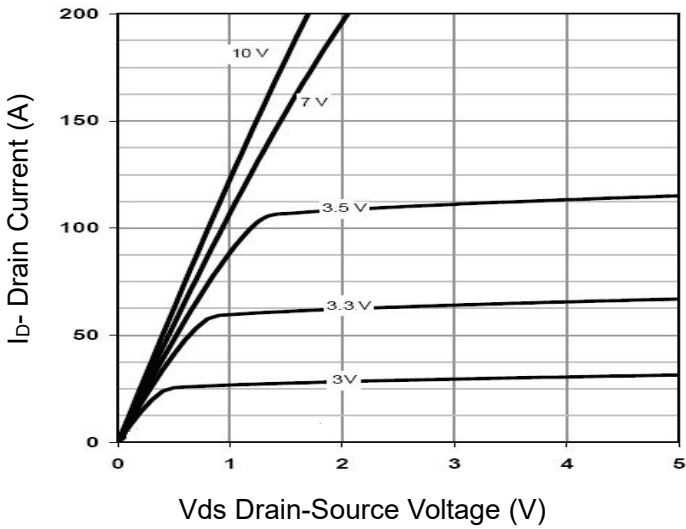
## Electrical Characteristics (T<sub>c</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	100		-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
<b>On Characteristics</b> (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1.1	1.7	2.5	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =32.5A	-	9	9.5	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =32.5A	-	11	12.5	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =32.5A		50	-	S
<b>Dynamic Characteristics</b> (Note3)						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =50V, V <sub>GS</sub> =0V, F=1.0MHz	-	2609	-	pF
Output Capacitance	C <sub>oss</sub>		-	247.5	-	pF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	17	-	pF
<b>Switching Characteristics</b> (Note 3)						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =50V, I <sub>D</sub> =32.5A V <sub>GS</sub> =10V, R <sub>G</sub> =1.6Ω	-	13	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	10	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	30	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	8	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =50V, I <sub>D</sub> =32.5A, V <sub>GS</sub> =10V	-	45	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	9.4	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	10.2	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 2)	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =32.5A	-	-	1.2	V
Diode Forward Current	I <sub>S</sub>		-	-	65	A
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25°C, I <sub>F</sub> = 32.5A di/dt = 100A/μs (Note3)	-	55	-	nS
Reverse Recovery Charge	Q <sub>rr</sub>		-	98	-	nC

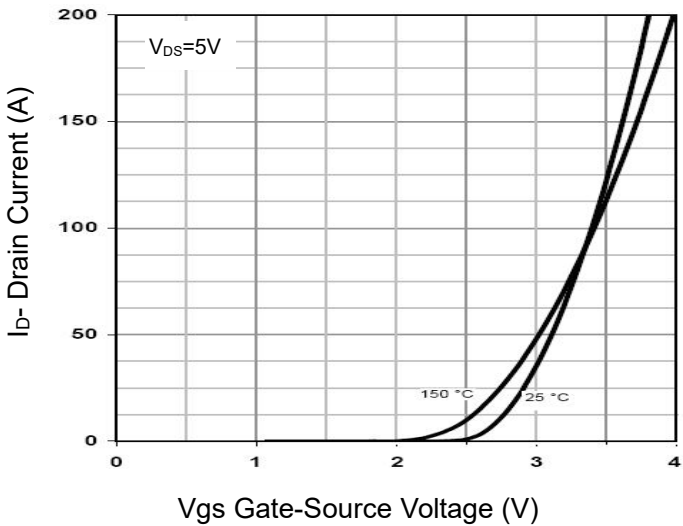
### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
3. Guaranteed by design, not subject to production
4. EAS condition : T<sub>J</sub>=25°C, V<sub>DD</sub>=50V, V<sub>G</sub>=10V, L=0.5mH, R<sub>G</sub>=25Ω

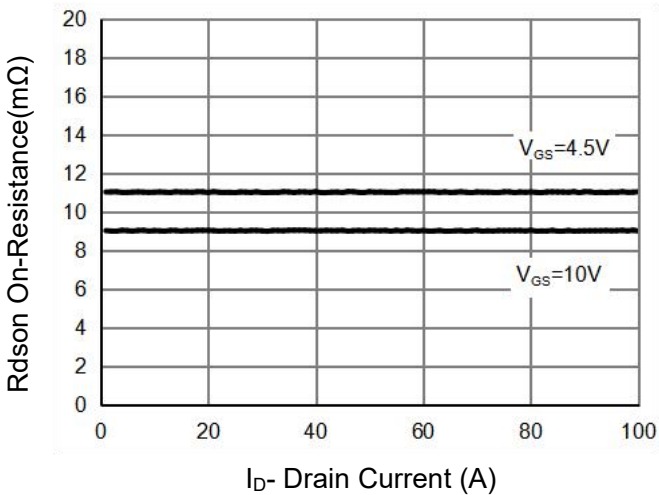
## Typical Electrical and Thermal Characteristics



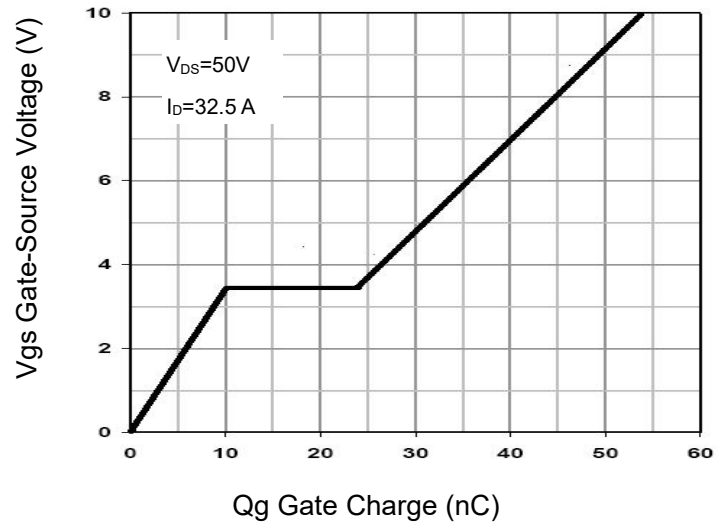
**Figure 1 Output Characteristics**



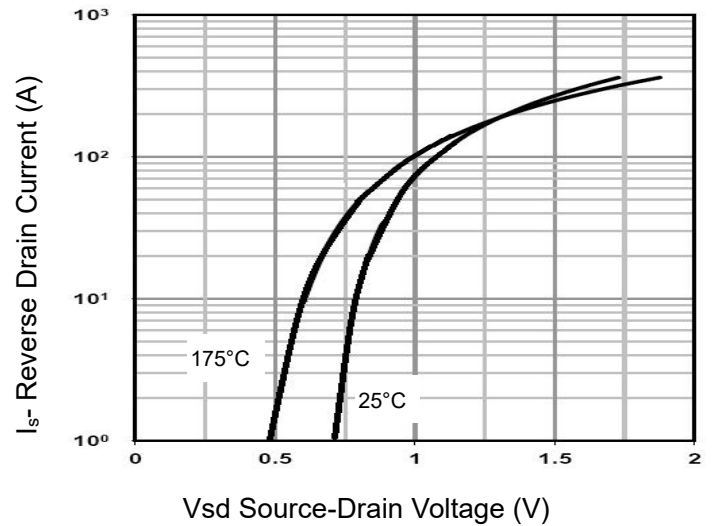
**Figure 2 Transfer Characteristics**



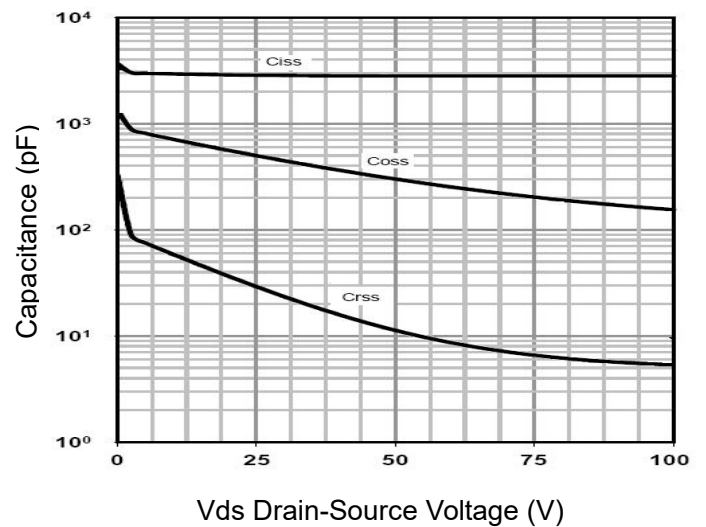
**Figure 3 Rdson- Drain Current**



**Figure 4 Gate Charge**



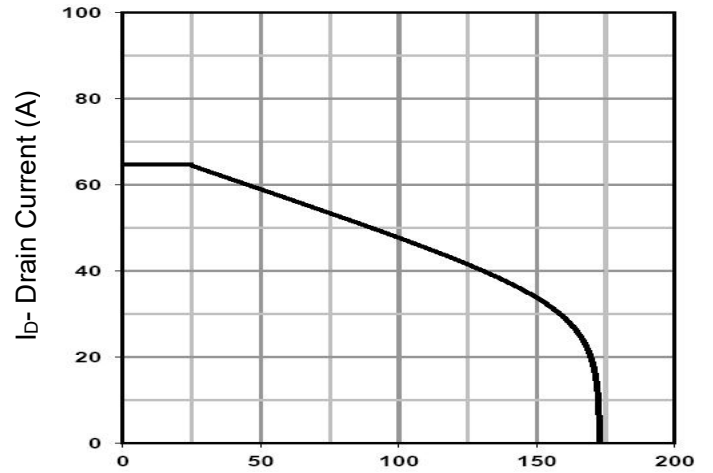
**Figure 5 Source- Drain Diode Forward**



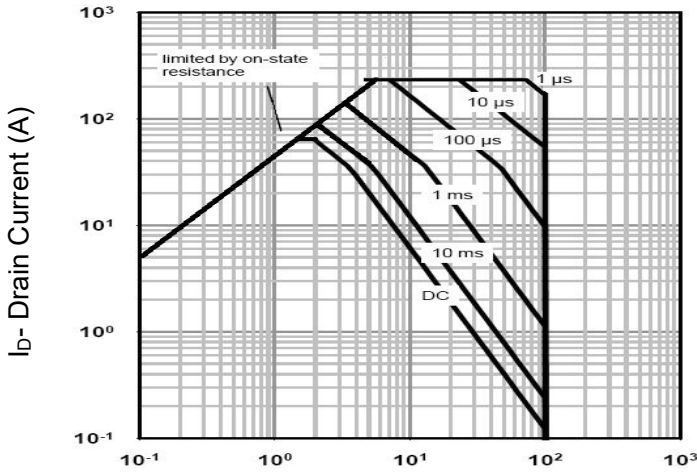
**Figure 6 Capacitance vs Vds**



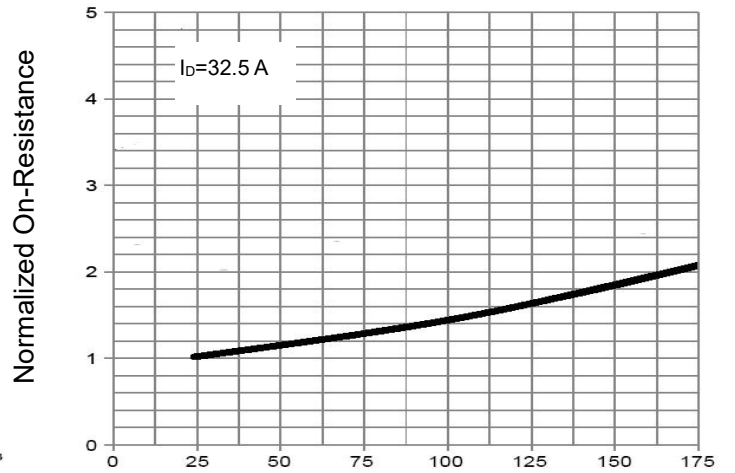
T<sub>J</sub>-Junction Temperature(°C)  
**Figure 7 Power De-rating**



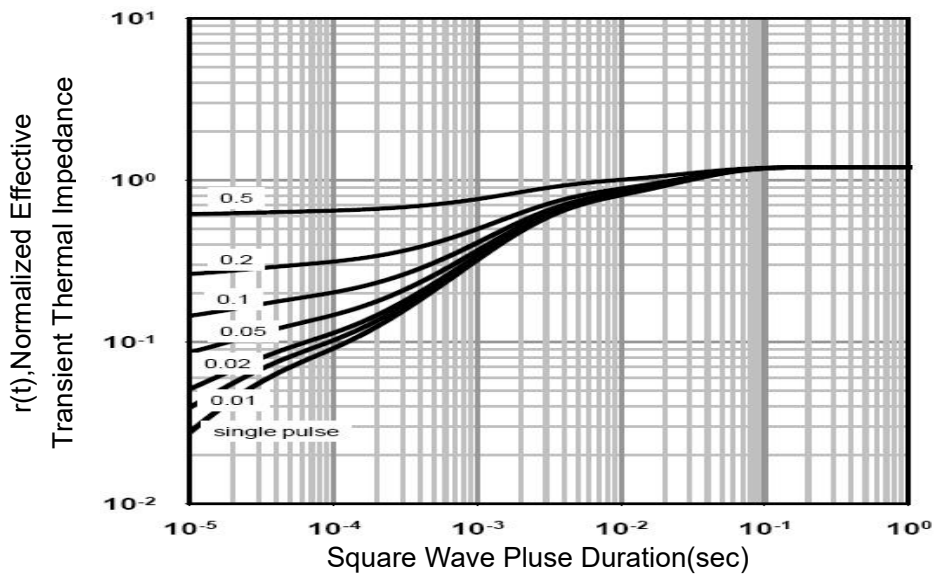
T<sub>J</sub>-Junction Temperature (°C)  
**Figure 9 Current De-rating**



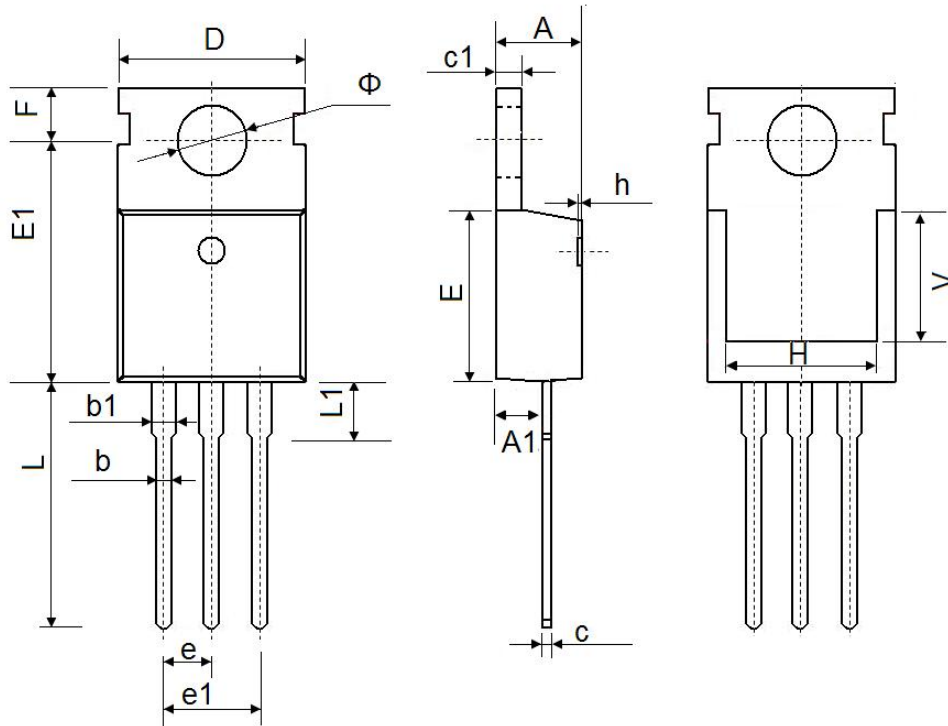
V<sub>DS</sub> Drain-Source Voltage (V)  
**Figure 8 Safe Operation Area**



T<sub>J</sub>-Junction Temperature(°C)  
**Figure 10 Rdson-Junction Temperature**



## TO-220-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.9500	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	6.900 REF.		0.276 REF.	
Φ	3.400	3.800	0.134	0.150

### Attention

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